

CCD linear image sensors



S11155-2048-01 S11156-2048-01

Back-thinned CCD image sensors with electronic shutter function

The S11155-2048-01 and S11156-2048-01 are back-thinned CCD linear image sensors with an internal electronic shutter for spectrometers. These image sensors use a resistive gate structure that allows high-speed transfer. Each pixel has a lengthwise size needed by spectrometers but ensures readout with low image lag.

Features

- Built-in electronic shutter
- Minimum integration time: 2 μ s
- High sensitivity from the ultraviolet region (spectral response range: 200 to 1100 nm)
- Readout speed: 10 MHz max.
- Image lag: 0.1% typ.

Applications

- Spectrometers
- Image readout

Structure

Parameter	S11155-2048-01	S11156-2048-01
Pixel size (H \times V)	14 \times 500 μ m	14 \times 1000 μ m
Number of total pixels (H \times V)	2068 \times 1	
Number of effective pixels (H \times V)	2048 \times 1	
Image size (H \times V)	28.672 \times 0.500 mm	28.672 \times 1.000 mm
Horizontal clock phase	2-phase	
Output circuit	Two-stage MOSFET source follower	
Package	24-pin ceramic DIP (refer to dimensional outline)	
Window*1	Quartz glass*2	
Cooling	Non-cooled	

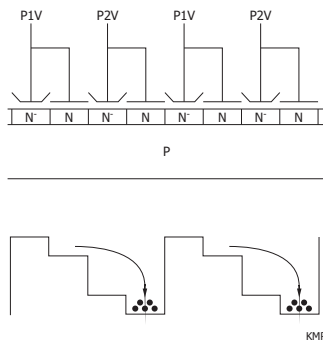
*1: Temporary window type (ex. S11155-2048N-01) is available upon request.

*2: Resin sealing

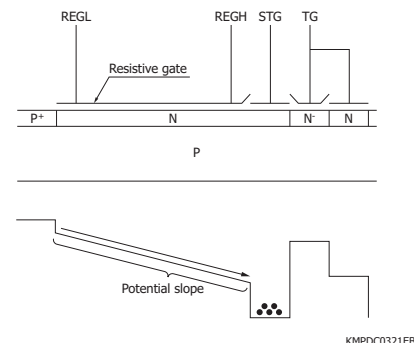
Resistive gate structure

In ordinary CCDs, one pixel contains multiple electrodes and a signal charge is transferred by applying different clock pulses to those electrodes [Figure 1]. In resistive gate structures, a single high-resistance electrode is formed in the active area, and a signal charge is transferred by means of a potential slope that is created by applying different voltages across the electrode [Figure 2]. Compared to a CCD area image sensor which is used as a linear sensor by line binning, a one-dimensional CCD having a resistive gate structure in the active area offers higher speed transfer, allowing readout with low image lag even if the pixel height is large.

[Figure 1] Schematic diagram and potential of ordinary 2-phase CCD



[Figure 2] Schematic diagram and potential of resistive gate structure



▣ Absolute maximum ratings (Ta=25 °C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	
Operating temperature*3 *4	Topr	-50	-	+50	°C	
Storage temperature	Tstg	-50	-	+70	°C	
Output transistor drain voltage	VOD	-0.5	-	+25	V	
Reset drain voltage	VRD	-0.5	-	+18	V	
Output amplifier return voltage	Vret	-0.5	-	+18	V	
All reset drain voltage	VARD	-0.5	-	+18	V	
Horizontal input source voltage	VISH	-0.5	-	+18	V	
All reset gate voltage	VARG	-10	-	+15	V	
Storage gate voltage	VSTG	-10	-	+15	V	
Horizontal input gate voltage	VIG1H, VIG2H	-10	-	+15	V	
Summing gate voltage	VSG	-10	-	+15	V	
Output gate voltage	VOG	-10	-	+15	V	
Reset gate voltage	VRG	-10	-	+15	V	
Transfer gate voltage	VTG	-10	-	+15	V	
Resistive gate voltage	High	VREGH	-10	-	+15	V
	Low	VREGL				
Horizontal shift register clock voltage	VP1H, VP2H	-10	-	+15	V	

*3: Package temperature

*4: The sensor temperature may increase due to heating in high-speed operation. We recommend taking measures to dissipate heat as needed. For more details, refer to the technical information “Resistive gate type CCD linear image sensors with electronic shutter”.

Note: Exceeding the absolute maximum ratings even momentarily may cause a drop in product quality. Always be sure to use the product within the absolute maximum ratings.

▣ Operating conditions (Ta=25 °C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	
Output transistor drain voltage	VOD	12	15	18	V	
Reset drain voltage	VRD	14	15	16	V	
All reset drain voltage	VARD	14	15	16	V	
All reset gate voltage	High*5	VARGH	7	8	9	V
	Low*6	VARGL	-2	-1.5	-1	
Output gate voltage	VOG	2.5	3	3.5	V	
Storage gate voltage	VSTG	-	0	-	V	
Substrate voltage	VSS	-	0	-	V	
Resistive gate high voltage	High	VREGHH	-4.5	-4	-3.5	V
	Low	VREGHL	-9	-8	-7	
Resistive gate low voltage	High	VREGLH	-	VREGHH - 2.5	-	V
	Low	VREGLL	-9	-8	-7	
Output amplifier return voltage*7	Vret	-	1	2	V	
Test point	Horizontal input source	VISH	-	VRD	-	V
	Horizontal input gate	VIG1H, VIG2H	-9	-8	-	V
Horizontal shift register clock voltage	High	VP1HH, VP2HH	4	5	6	V
	Low	VP1HL, VP2HL	-8	-7	-6	
Summing gate voltage	High	VSGH	4	5	6	V
	Low	VSGL	-8	-7	-6	
Reset gate voltage	High	VRGH	7	8	9	V
	Low	VRGL	-6	-5	-4	
Transfer gate voltage	High	VTGH	8.5	9	9.5	V
	Low	VTGL	-7.5	-7	-6.5	
External load resistance	RL	2.0	2.2	2.4	kΩ	

*5: All reset on

*6: All reset off

*7: Output amplifier return voltage is a positive voltage with respect to Substrate voltage, but the current flows in the direction of flow out of the sensor.

Electrical characteristics (Ta=25 °C)

Parameter		Symbol	Min.	Typ.	Max.	Unit
Signal output frequency		fc	-	5	10	MHz
Line rate		LR	-	2	4	kHz
Horizontal shift register capacitance		CP1H, CP2H	-	200	-	pF
All reset gate capacitance		CARG	-	100	-	pF
Resistive gate capacitance	S11155-2048-01	CREG	-	1000	-	pF
	S11156-2048-01		-	2000	-	
Summing gate capacitance		CSG	-	10	-	pF
Reset gate capacitance		CRG	-	10	-	pF
Transfer gate capacitance		CTG	-	100	-	pF
Charge transfer efficiency*8		CTE	0.99995	0.99999	-	-
DC output level		Vout	7	8	9	V
Output impedance		Zo	-	300	-	Ω
Output amplifier return current		Iret	-	0.4	-	mA
Power consumption	S11155-2048-01	PAMP*9	-	75	-	mW
		PREG*10	1.4	2.5	12.5	
	S11156-2048-01	PAMP*9	-	75	-	
		PREG*10	0.7	1.3	6.3	
Resistive gate resistance*11	S11155-2048-01	RREG	0.5	2.5	4.5	kΩ
	S11156-2048-01		1	5	9	

*8: Charge transfer efficiency per pixel of CCD shift register, measured at half of the full well capacity

*9: Power consumption of the on-chip amplifier plus load resistance

*10: Power consumption at REG

*11: Resistance value between REGH and REGL

Electrical and optical characteristics (Ta=25 °C, unless otherwise noted)

Parameter	Symbol	S11155-2048-01			S11156-2048-01			Unit	
		Min.	Typ.	Max.	Min.	Typ.	Max.		
Saturation output voltage	Vsat	-	Fw x Sv	-	-	Fw x Sv	-	V	
Full well capacity*12	Fw	-	200	-	-	200	-	ke ⁻	
CCD node sensitivity	Sv	7	8	9	7	8	9	μV/e ⁻	
Dark current*13	Non-MPP operation	DS	-	50	300	-	100	600	ke ⁻ /pixel/s
	MPP operation		-	4	16	-	8	32	
Readout noise*14	Nr	-	30	45	-	30	45	e ⁻ rms	
Dynamic range*15	DR	-	6670	-	-	6670	-	-	
Spectral response range	λ	-	200 to 1100	-	-	200 to 1100	-	nm	
Photoresponse nonuniformity*16 *17	PRNU	-	±3	±10	-	±3	±10	%	
Image lag*16 *18	L	-	0.1	1	-	0.1	1	%	

*12: Operating voltages typ.

*13: Dark current is reduced to half for every 5 to 7 °C decrease in temperature.

*14: Readout frequency is 2 MHz

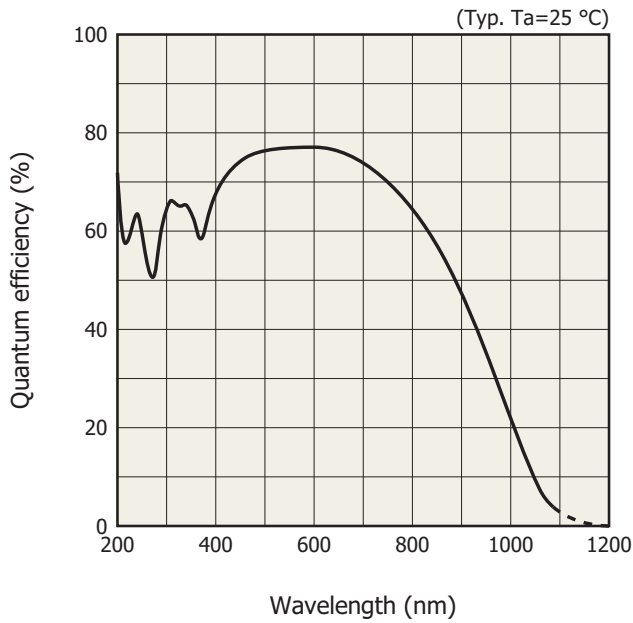
*15: Dynamic range (DR) = Full well capacity / Readout noise

*16: Measured at one-half of the saturation output (full well capacity) using LED light (peak emission wavelength: 660 nm)

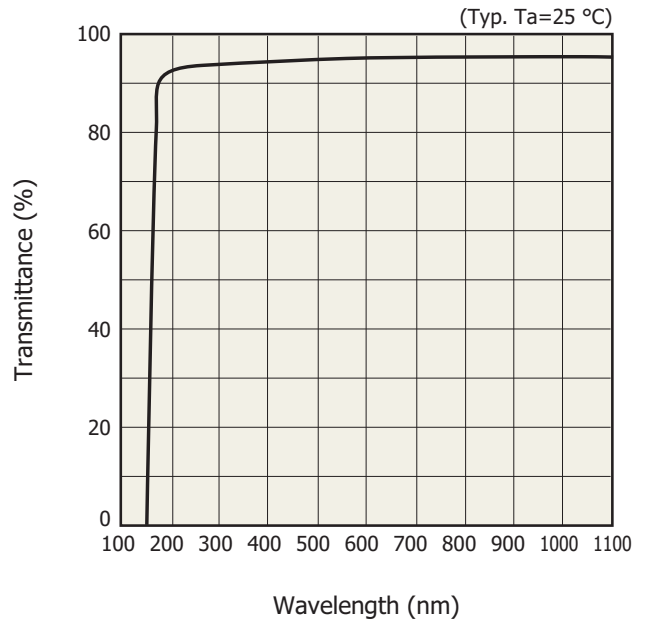
*17: Photoresponse nonuniformity = $\frac{\text{Fixed pattern noise (peak to peak)}}{\text{Signal}} \times 100$ [%]

*18: The ratio of remaining signal after the image sensor is illuminated with one shot of pulsed light that produces one-half of the saturation output. For more details refer to our technical information on "Resistive gate type CCD linear image sensors with electronic shutter."

Spectral response (without window)*19

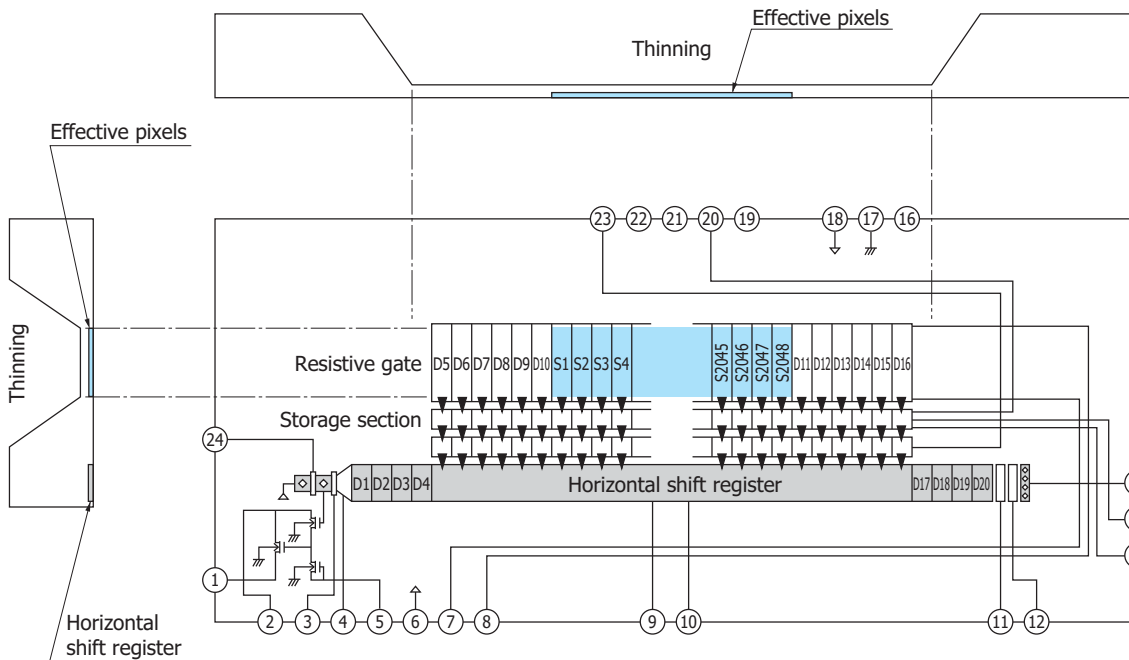


Spectral transmittance characteristic of window material



*19: Spectral response with quartz glass is decreased according to the spectral transmittance characteristic of window material.

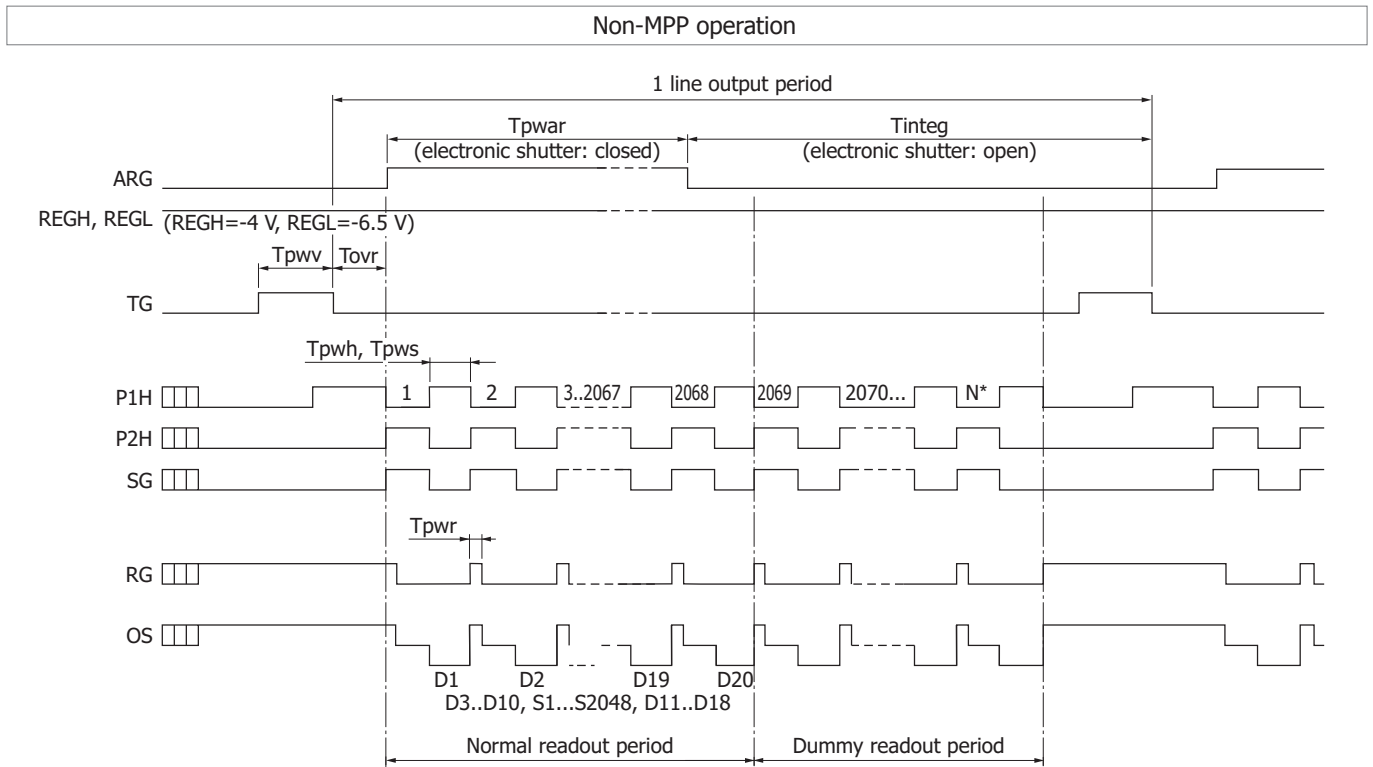
Device structure (conceptual drawing of top view in dimensional outline)



Note: When viewed from the direction of the incident light, the horizontal shift register is covered with a thick silicon layer (dead layer). However, long-wavelength light passes through the silicon dead layer and may possibly be detected by the horizontal shift register. To prevent this, provide light shield on that area as needed.

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Timing chart



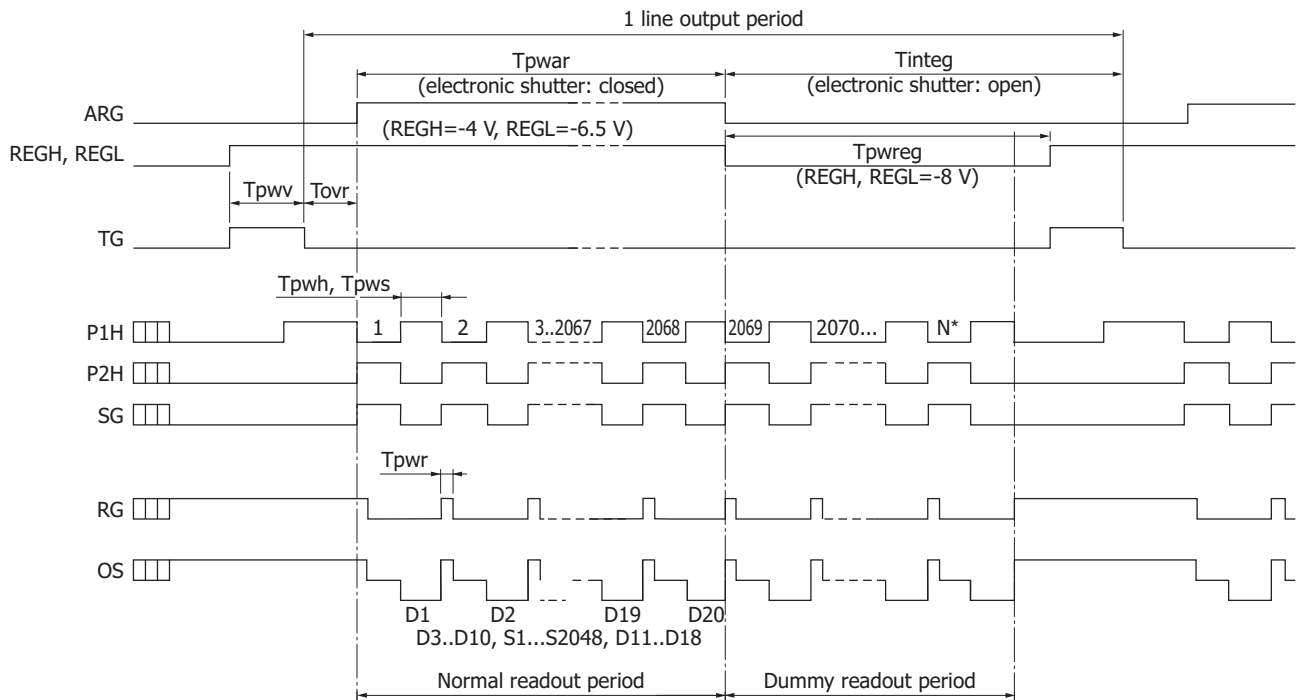
* Apply clock pulses to the specified terminals during the period of dummy readout. Set the total number of clock pulses N, according to the integration time.

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Parameter		Symbol	Min.	Typ.	Max.	Unit
ARG	Pulse width	Tpwar	1	-	-	μs
	Rise and fall times	Tprar, Tpfar	200	-	-	ns
TG	Pulse width	Tpww	2	-	-	μs
	Rise and fall times	Tprv, Tpfv	20	-	-	ns
P1H, P2H*20	Pulse width	Tpwh	50	100	-	ns
	Rise and fall times	Tprh, Tpfh	10	-	-	ns
	Duty ratio	-	40	50	60	%
SG	Pulse width	Tpws	50	100	-	ns
	Rise and fall times	Tprs, Tpfs	10	-	-	ns
	Duty ratio	-	40	50	60	%
RG	Pulse width	Tpwr	5	15	-	ns
	Rise and fall times	Tpr, Tprf	5	-	-	ns
TG - P1H	Overlap time	Tovr	1	2	-	μs
Integration time		Tinteg	2	-	-	μs

*20: Symmetrical clock pulses should be overlapped at 50% of maximum pulse amplitude.

MPP operation



* Apply clock pulses to the specified terminals during the period of dummy readout. Set the total number of clock pulses N, according to the integration time.

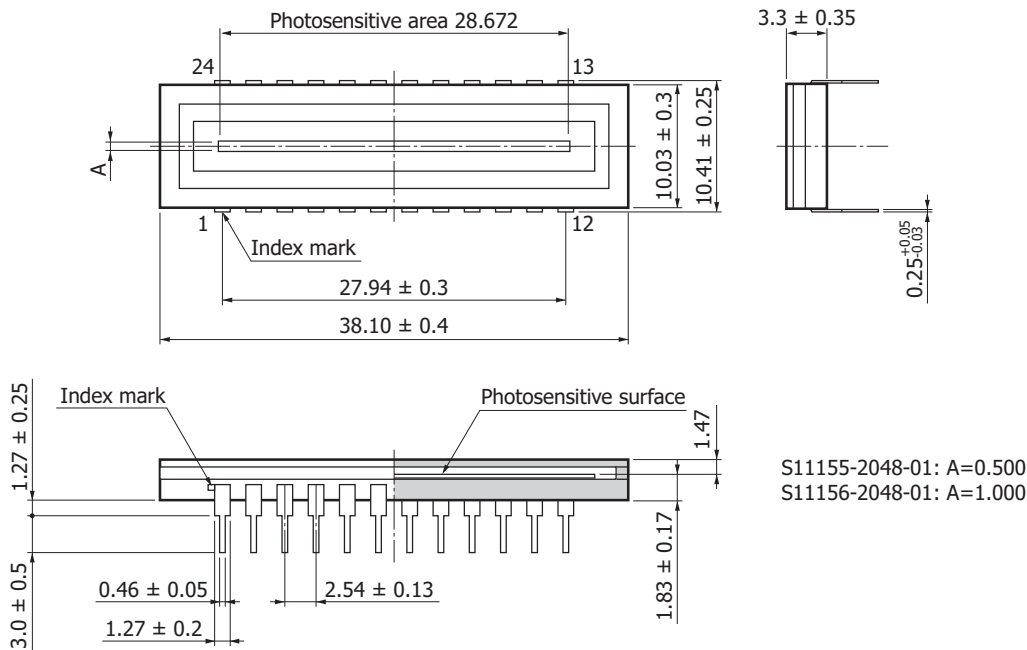
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Parameter		Symbol	Min.	Typ.	Max.	Unit
ARG	Pulse width	T_{pwar}	*21	-	-	μs
	Rise and fall times	T_{prar}, T_{pfar}	200	-	-	ns
REGH, REGL	Pulse width	T_{pwreg}	-	$T_{integ} - T_{pww}$	-	μs
	Rise and fall times	T_{prreg}, T_{pfreg}	100	-	-	ns
TG	Pulse width	T_{pww}	2	-	-	μs
	Rise and fall times	T_{prv}, T_{pfv}	20	-	-	ns
P1H, P2H*22	Pulse width	T_{pwh}	50	100	-	ns
	Rise and fall times	T_{prh}, T_{pfh}	10	-	-	ns
	Duty ratio	-	40	50	60	%
SG	Pulse width	T_{pws}	50	100	-	ns
	Rise and fall times	T_{prs}, T_{pfs}	10	-	-	ns
	Duty ratio	-	40	50	60	%
RG	Pulse width	T_{pwr}	5	15	-	ns
	Rise and fall times	T_{pr}, T_{pfr}	5	-	-	ns
TG - P1H	Overlap time	T_{ovr}	1	2	-	μs
Integration time		T_{integ}	2	-	-	μs

*21: The Min. value of T_{pwar} is equal to the normal readout period.

*22: Symmetrical clock pulses should be overlapped at 50% of maximum pulse amplitude.

Dimensional outline (unit: mm)



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Pin connections

Pin no.	Symbol	Function	Remark (standard operation)
1	OS	Output transistor source	RL=2.2 kΩ
2	OD	Output transistor drain	+15 V
3	OG	Output gate	+3 V
4	SG	Summing gate	Same pulse as P2H
5	Vret	Output amplifier return	+1 V
6	RD	Reset drain	+15 V
7	REGL	Resistive gate (low)	-6.5 V (Non-MPP operation)
8	REGH	Resistive gate (high)	-4 V (Non-MPP operation)
9	P2H	CCD horizontal register clock-2	
10	P1H	CCD horizontal register clock-1	
11	IG2H	Test point (horizontal input gate-2)	-8 V
12	IG1H	Test point (horizontal input gate-1)	-8 V
13	ARG	All reset gate	
14	ARD	All reset drain	+15 V
15	ISH	Test point (horizontal input source)	Connect to RD
16	-		
17	SS	Substrate	GND
18	RD	Reset drain	+15 V
19	-		
20	STG	Storage gate	0 V
21	-		
22	-		
23	TG	Transfer gate	
24	RG	Reset gate	

Related information

www.hamamatsu.com/sp/ssd/doc_en.html

■ Precautions

- Notice
- Image sensors/Precautions

■ Technical information

- Resistive gate type CCD linear image sensors with electronic shutter/Technical information

Driver circuits for CCD linear image sensor (S11155-2048-01, S11156-2048-01) C11165-01 [sold separately]

The C11165-01 is a driver circuit designed for HAMAMATSU CCD linear image sensors S11155-2048-01, S11156-2048-01. The C11165-01 can be used in spectrometer when combined with the CCD linear image sensor.

Features

- **Built-in 16-bit A/D converter**
- **Interface of computer: USB 2.0**
- **Operates by DC+5 V**



Information described in this material is current as of July, 2014.

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The product warranty is valid for one year after delivery and is limited to product repair or replacement for defects discovered and reported to us within that one year period. However, even if within the warranty period we accept absolutely no liability for any loss caused by natural disasters or improper product use.

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HAMAMATSU

www.hamamatsu.com

HAMAMATSU PHOTONICS K.K., Solid State Division

1126-1 Ichino-cho, Higashi-ku, Hamamatsu City, 435-8558 Japan, Telephone: (81) 53-434-3311, Fax: (81) 53-434-5184

U.S.A.: Hamamatsu Corporation: 360 Foothill Road, Bridgewater, N.J. 08807, U.S.A., Telephone: (1) 908-231-0960, Fax: (1) 908-231-1218

Germany: Hamamatsu Photonics Deutschland GmbH: Arzbergerstr. 10, D-82211 Herrsching am Ammersee, Germany, Telephone: (49) 8152-375-0, Fax: (49) 8152-265-8

France: Hamamatsu Photonics France S.A.R.L.: 19, Rue du Saule Trapu, Parc du Moulin de Massy, 91882 Massy Cedex, France, Telephone: 33-(1) 69 53 71 00, Fax: 33-(1) 69 53 71 10

United Kingdom: Hamamatsu Photonics UK Limited: 2 Howard Court, 10 Tewin Road, Welwyn Garden City, Hertfordshire AL7 1BW, United Kingdom, Telephone: (44) 1707-294888, Fax: (44) 1707-325777

North Europe: Hamamatsu Photonics Norden AB: Torshamnsgatan 35 16440 Kista, Sweden, Telephone: (46) 8-509-031-00, Fax: (46) 8-509-031-01

Italy: Hamamatsu Photonics Italia S.r.l.: Strada della Moia, 1 int. 6, 20020 Arese (Milano), Italy, Telephone: (39) 02-93581733, Fax: (39) 02-93581741

China: Hamamatsu Photonics (China) Co., Ltd.: B1201, Jiaming Center, No.27 Dongsanhuan Beilu, Chaoyang District, Beijing 100020, China, Telephone: (86) 10-6586-6006, Fax: (86) 10-6586-2866